Silicon PNP Power Transistors 2SA1205

DESCRIPTION

- With TO-3PN package
- High power dissipation

APPLICATIONS

- For general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

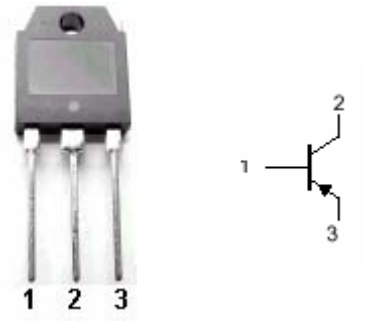


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-12	A
I_B	Base current		-4	A
P_C	Collector power dissipation	T_C=25℃	100	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-25mA ;I_B=0	-50			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A; I_B=-0.12A			-0.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-70V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-0.1	mA
h_{FE}	DC current gain	I_C=-5A ; V_{CE}=-0.5V	40			
f_T	Transition frequency	I_E=3A ; V_{CE}=-12V		20		MHz

Switching times

t_{on}	Turn-on time	I_C=-5A;R_L=4 Ω I_{B1}=-I_{B2}=-0.12A V_{CC}=-20V		0.60		μ s
t_{stg}	Storage time			0.50		μ s
t_f	Fall time			0.25		μ s

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PACKAGE OUTLINE

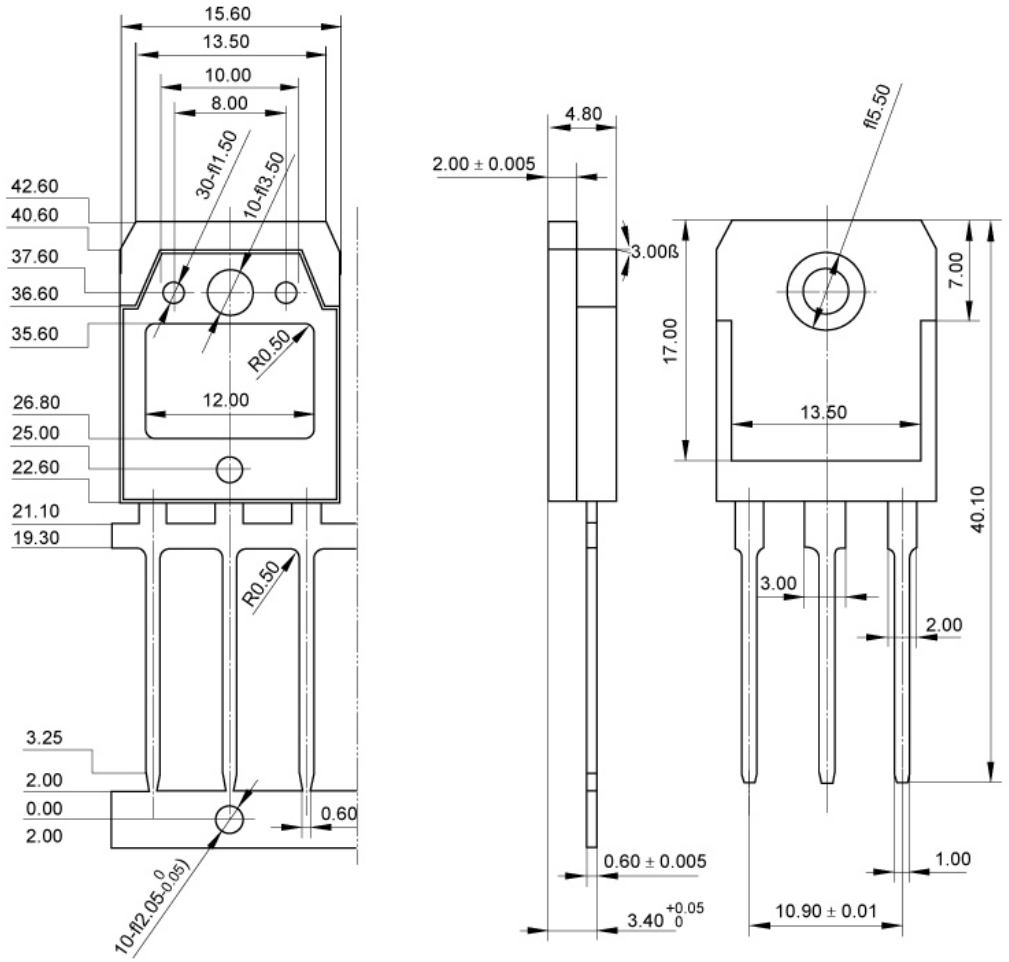


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)